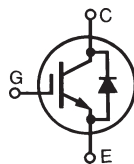


**High Voltage, High Gain
BiMOSFET™ Monolithic
Bipolar MOS Transistor**
**IXBA12N300HV
IXBT12N300HV**

$$V_{CES} = 3000V$$

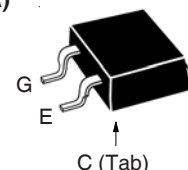
$$I_{C110} = 12A$$

$$V_{CE(sat)} \leq 3.2V$$

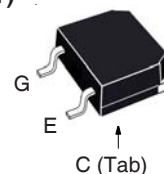


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $150^\circ C$	3000	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	3000	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$	30	A
I_{C110}	$T_C = 110^\circ C$	12	A
I_{CM}	$T_C = 25^\circ C$, 1ms	100	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 125^\circ C$, $R_G = 30\Omega$ Clamped Inductive Load	$I_{CM} = 98$ 1500	A V
P_C	$T_C = 25^\circ C$	160	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
Weight	TO-263	2.5	g
	TO-268	4.0	g

TO-263 (IXBA)



TO-268 (IXBT)


 G = Gate
E = Emitter

 C = Collector
Tab = Collector

Features

- High Voltage Package
- High Blocking Voltage
- Anti-Parallel Diode
- Low Conduction Losses

Advantages

- Low Gate Drive Requirement
- High Power Density

Applications:

- Switch-Mode and Resonant-Mode Power Supplies
- Uninterruptible Power Supplies (UPS)
- Laser Generators
- Capacitor Discharge Circuits
- AC Switches

Symbol	Test Conditions ($T_J = 25^\circ C$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	3000		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$, $V_{GE} = 0V$ $T_J = 125^\circ C$			25 μA 1 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 12A$, $V_{GE} = 15V$, Note 1 $T_J = 125^\circ C$		2.8	3.2 V
			3.5	V

Symbol Test Conditions

($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

		Min.	Typ.	Max.		
g_{fS}	$I_C = 12\text{A}, V_{CE} = 10\text{V}, \text{Note 1}$	6.5	10.8		S	
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		1290		pF	
C_{oes}			56		pF	
C_{res}			19		pF	
$Q_{g(on)}$	$I_C = 12\text{A}, V_{GE} = 15\text{V}, V_{CE} = 1000\text{V}$		62		nC	
Q_{ge}			13		nC	
Q_{gc}			8.5		nC	
$t_{d(on)}$	Resistive Switching Times, $T_J = 25^\circ\text{C}$ $I_C = 12\text{A}, V_{GE} = 15\text{V}$		64		ns	
t_r			140		ns	
$t_{d(off)}$		$V_{CE} = 1250\text{V}, R_G = 10\Omega$		180		ns
t_f				540		ns
$t_{d(on)}$	Resistive Switching Times, $T_J = 125^\circ\text{C}$ $I_C = 12\text{A}, V_{GE} = 15\text{V}$		65		ns	
t_r			395		ns	
$t_{d(off)}$		$V_{CE} = 1250\text{V}, R_G = 10\Omega$		175		ns
t_f				530		ns
R_{thJC}				0.78	$^\circ\text{C/W}$	

Reverse Diode

Symbol Test Conditions

($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

		Min.	Typ.	Max.	
V_F	$I_F = 12\text{A}, V_{GE} = 0\text{V}$			2.1	V
t_{rr}	$I_F = 6\text{A}, V_{GE} = 0\text{V}, -di_F/dt = 100\text{A}/\mu\text{s}$		1.4		μs
I_{RM}		$V_R = 100\text{V}, V_{GE} = 0\text{V}$		21	

Note 1: Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

PRELIMINARY TECHNICAL INFORMATION

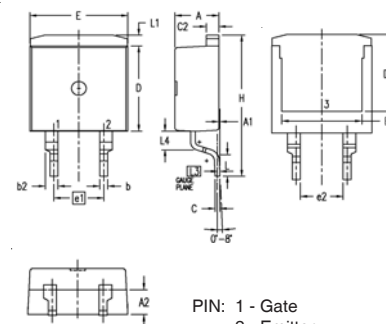
The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

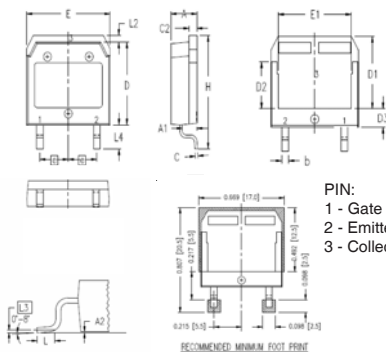
TO-263 (HV) Outline



PIN: 1 - Gate
2 - Emitter
3 - Collector

SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.170	.185	4.30	4.70
A1	.000	.008	0.00	0.20
A2	.091	.098	2.30	2.50
b	.028	.035	0.70	0.90
b2	.046	.054	1.18	1.38
C	.018	.024	0.45	0.60
C2	.049	.055	1.25	1.40
D	.354	.370	9.00	9.40
D1	.311	.327	7.90	8.30
E	.386	.402	9.80	10.20
E1	.307	.323	7.80	8.20
e1	.200 BSC		5.08 BSC	
(e2)	.163	.174	4.13	4.43
H	.591	.614	15.00	15.60
L	.079	.102	2.00	2.60
L1	.039	.055	1.00	1.40
L3	.010 BSC		0.254 BSC	
(L4)	.071	.087	1.80	2.20

TO-268 (HV) Outline



PIN:
1 - Gate
2 - Emitter
3 - Collector

SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.465	.476	11.80	12.10
D2	.295	.307	7.50	7.80
D3	.114	.126	2.90	3.20
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
(e)	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.067	.079	1.70	2.00
L2	.039	.045	1.00	1.15
(L3)	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

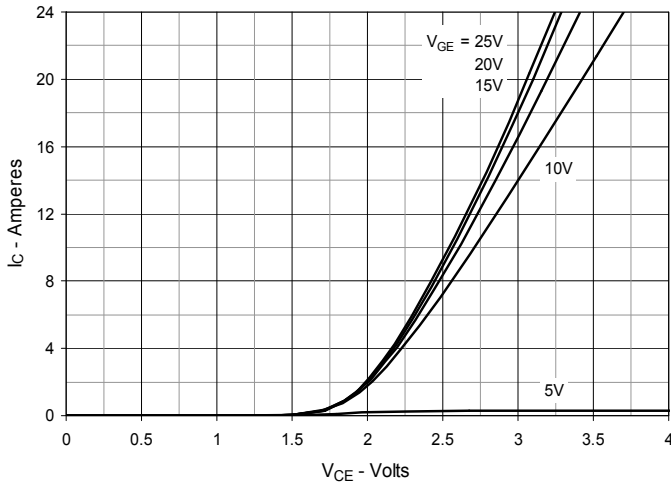


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

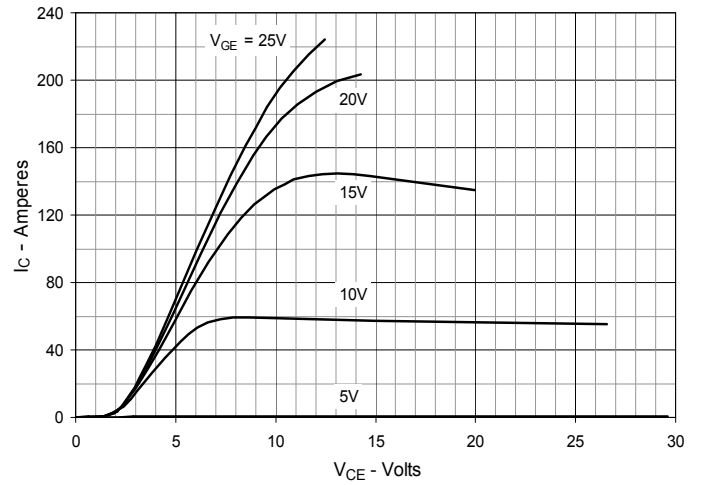


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

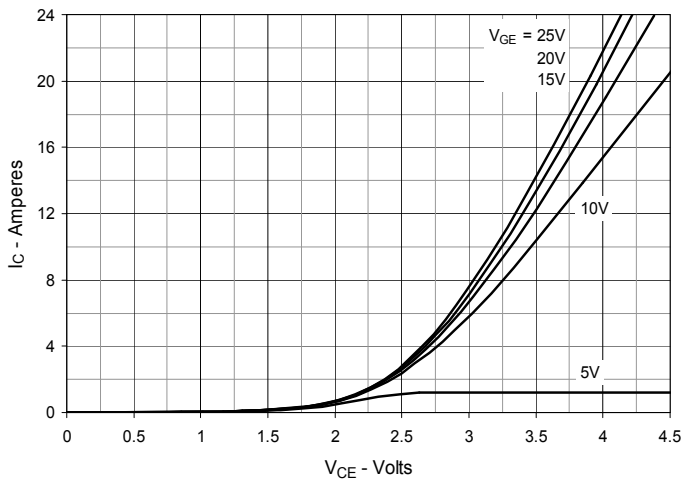


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

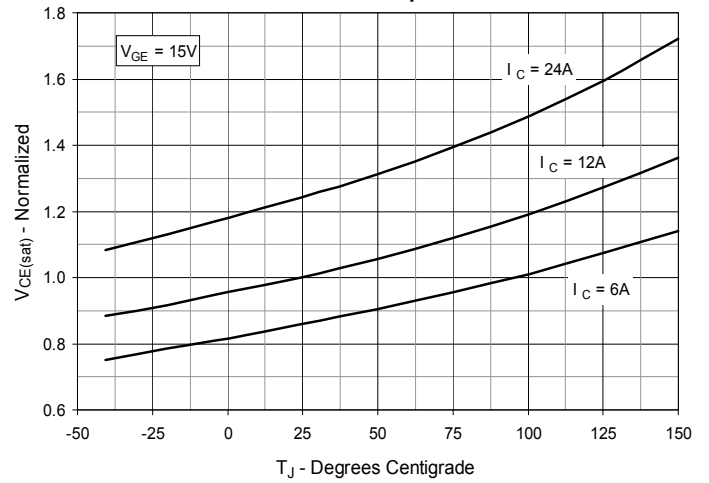


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

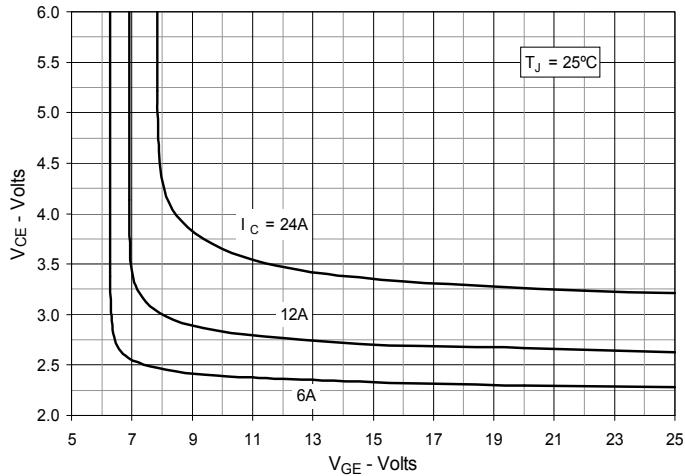


Fig. 6. Input Admittance

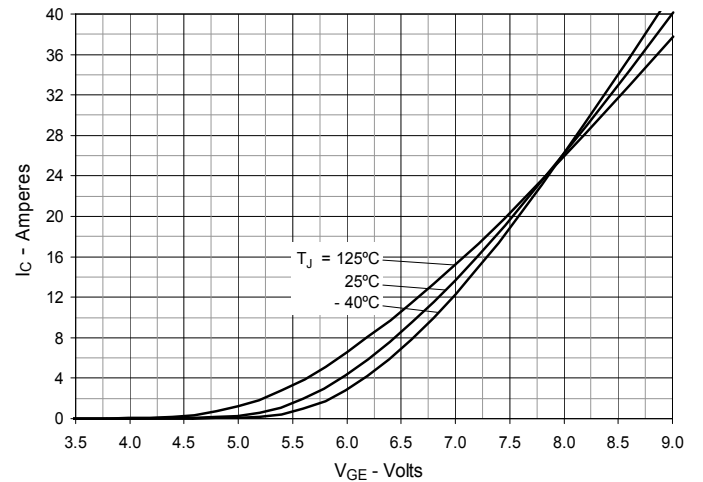


Fig. 7. Transconductance

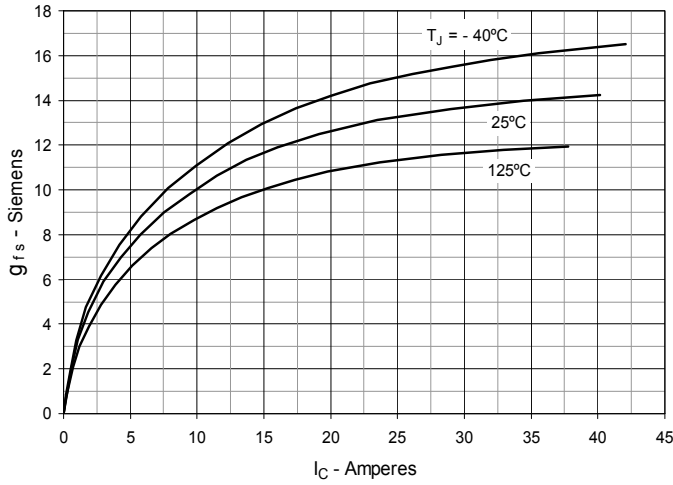


Fig. 8. Forward Voltage Drop of Intrinsic Diode

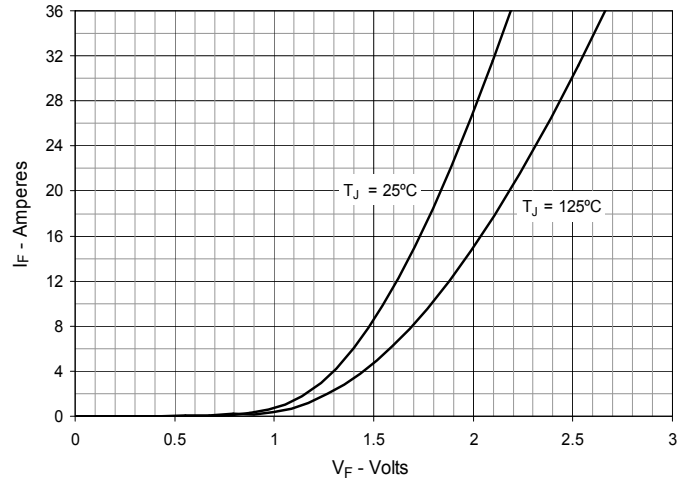


Fig. 9. Gate Charge

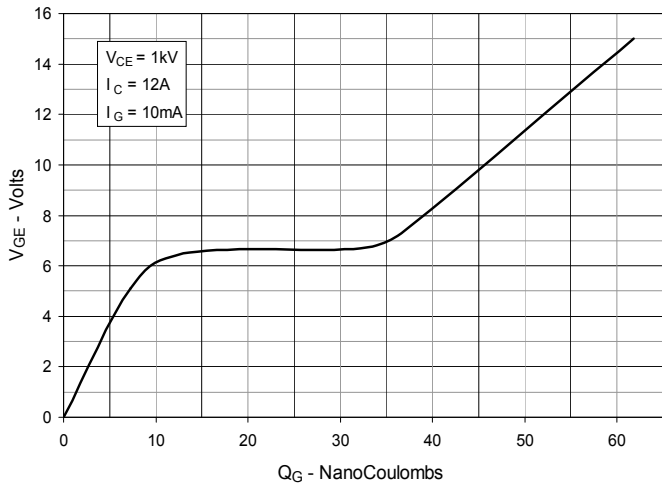


Fig. 10. Capacitance

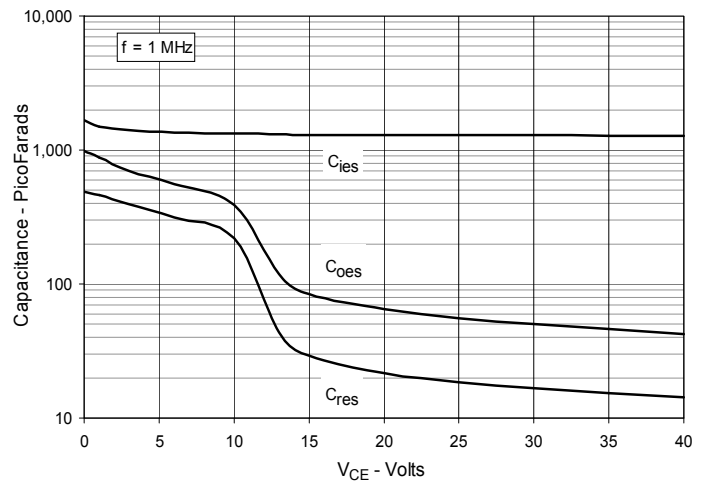


Fig. 11. Reverse-Bias Safe Operating Area

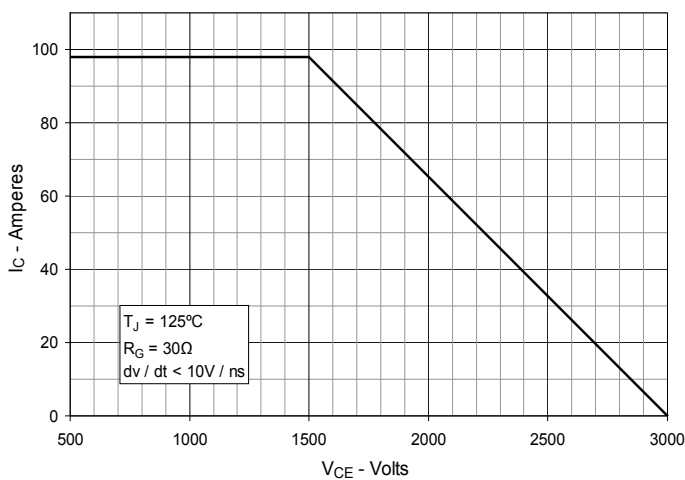


Fig. 12. Maximum Transient Thermal Impedance

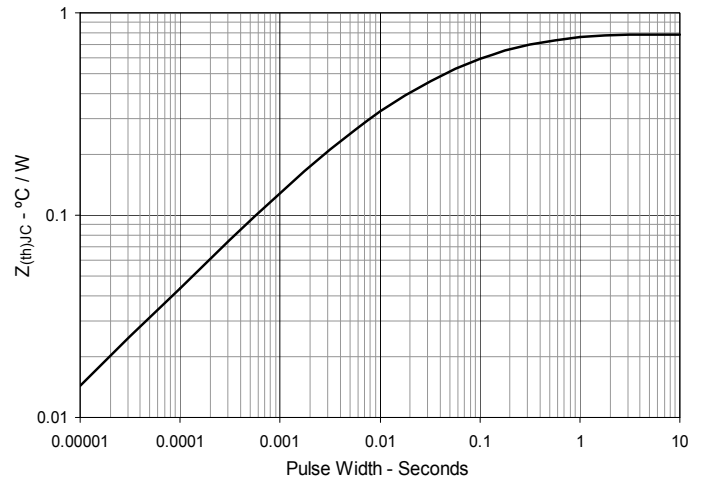


Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

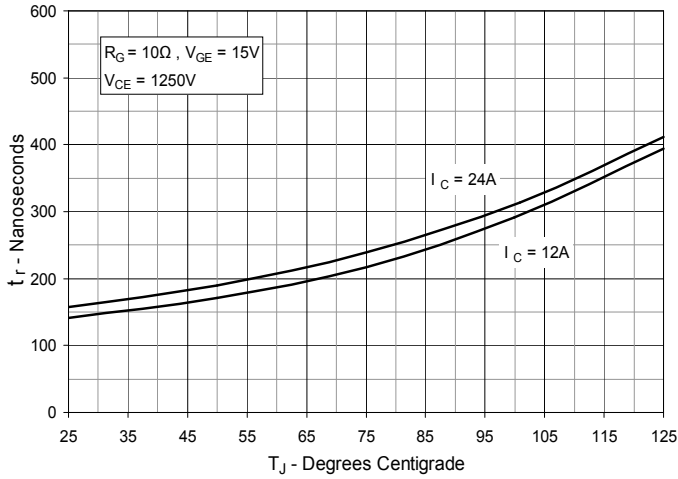


Fig. 14. Resistive Turn-on Rise Time vs. Collector Current

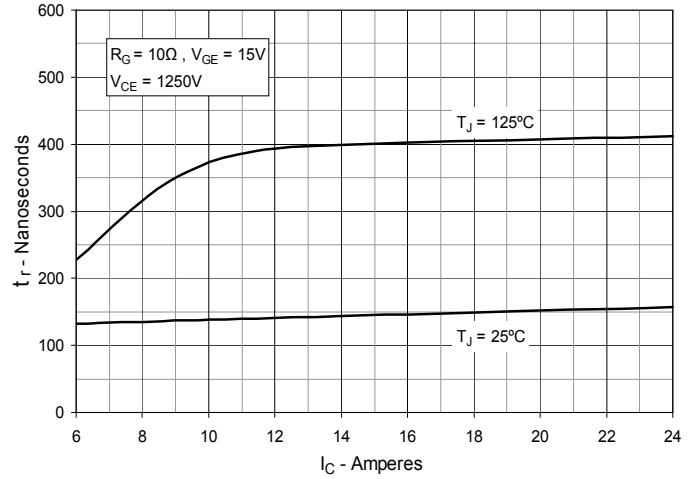


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

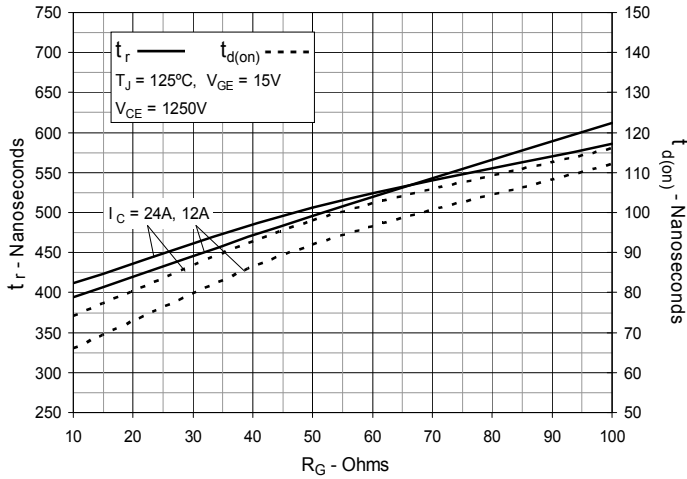


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

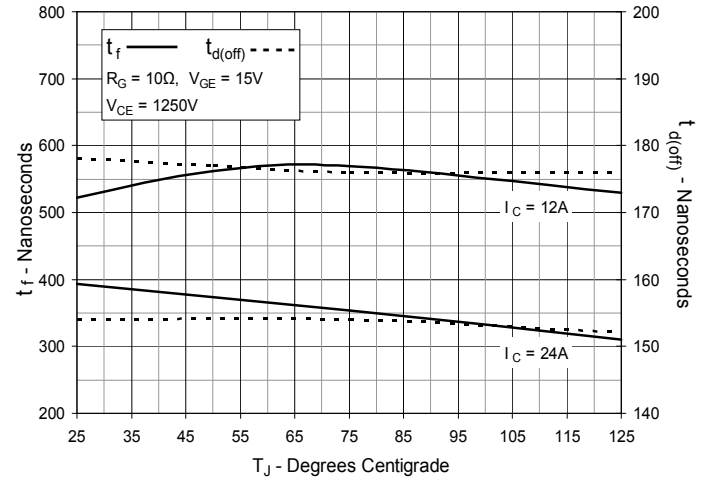


Fig. 17. Resistive Turn-off Switching Times vs. Collector Current

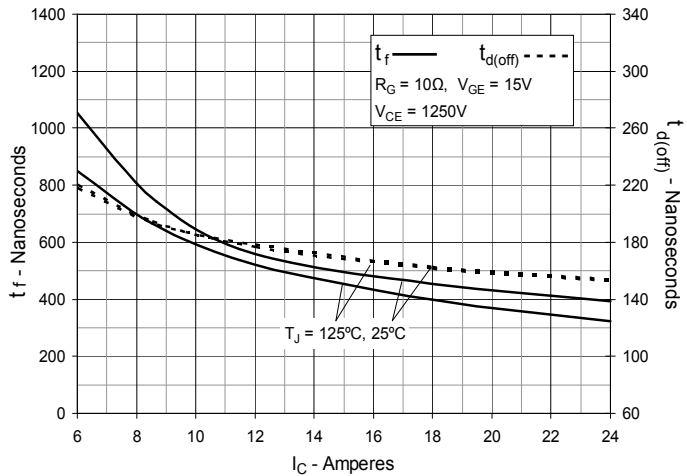
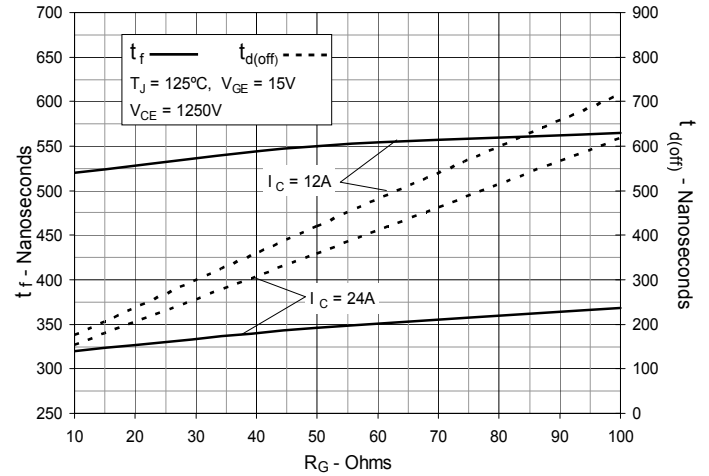


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance



Компания «Life Electronics» занимается поставками электронных компонентов импортного и отечественного производства от производителей и со складов крупных дистрибьюторов Европы, Америки и Азии.

С конца 2013 года компания активно расширяет линейку поставок компонентов по направлению коаксиальный кабель, кварцевые генераторы и конденсаторы (керамические, пленочные, электролитические), за счёт заключения дистрибьюторских договоров

Мы предлагаем:

- Конкурентоспособные цены и скидки постоянным клиентам.
- Специальные условия для постоянных клиентов.
- Подбор аналогов.
- Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.
- Приемлемые сроки поставки, возможна ускоренная поставка.
- Доставку товара в любую точку России и стран СНГ.
- Комплексную поставку.
- Работу по проектам и поставку образцов.
- Формирование склада под заказчика.
- Сертификаты соответствия на поставляемую продукцию (по желанию клиента).
- Тестирование поставляемой продукции.
- Поставку компонентов, требующих военную и космическую приемку.
- Входной контроль качества.
- Наличие сертификата ISO.

В составе нашей компании организован Конструкторский отдел, призванный помогать разработчикам, и инженерам.

Конструкторский отдел помогает осуществить:

- Регистрацию проекта у производителя компонентов.
- Техническую поддержку проекта.
- Защиту от снятия компонента с производства.
- Оценку стоимости проекта по компонентам.
- Изготовление тестовой платы монтаж и пусконаладочные работы.



Тел: +7 (812) 336 43 04 (многоканальный)

Email: org@lifeelectronics.ru